

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

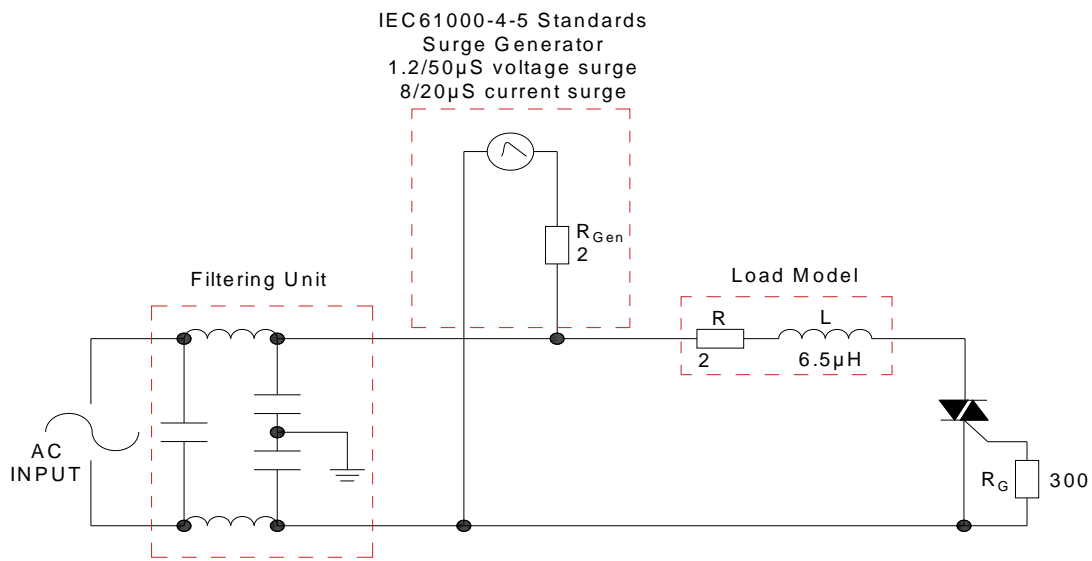
Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
I_H	$I_T=500mA$		MAX.	40	mA

dV/dt $V_D=400V$ Gate Open T_j
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ORDERING INFORMATION

JST16F-600CW

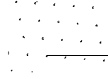
FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note "Assembly Instructions for Thyristors in Through-hole Package" released by JieJie
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PACKAGE MECHANICAL DATA



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